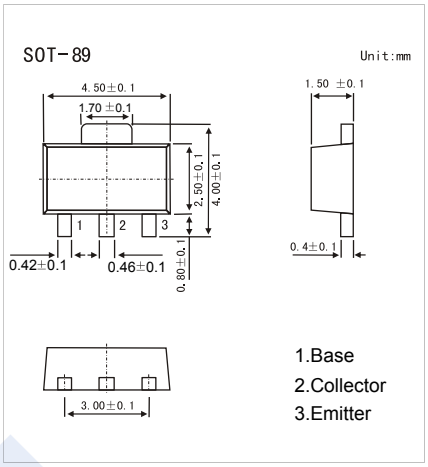
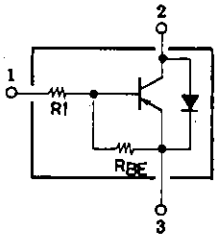
PNP Transistors

2SB1394



■ Features

- Contains diode between collector and emitter.
- Low saturation voltage.
- Large current capacity.
- Complementary to 2SD2099



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-40	V
Collector - Emitter Voltage	V_{CEO}	-30	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	-3	A
Collector Current - Pulse	I_{CP}	-5	
Collector Power Dissipation	P_C	1.5	W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-40			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA, R_{BE}=∞	-30			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C=0	-6			
Collector-base cut-off current	I_{CBO}	V_{CB}= -35 V , I_E=0			-1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-1 A, I_B=-50mA			-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-1 A, I_B=-50mA			-1.2	
DC current gain	$h_{FE(1)}$	V_{CE}= -2V, I_C= -500mA	70			
	$h_{FE(2)}$	V_{CE}=- 2V, I_C= -2 A	50			
Base-to-Emitter Resistance	R_{BE}			0.8		kΩ
Base Resistance	R_1		60		120	Ω
Diode Forwad Voltage	V_F	I_F=500mA			1.5	V
Collector output capacitance	C_{ob}	V_{CB}= -10V, I_E= 0,f=1MHz		55		pF
Transition frequency	f_T	V_{CE}= -2V, I_C= -500mA		100		MHz

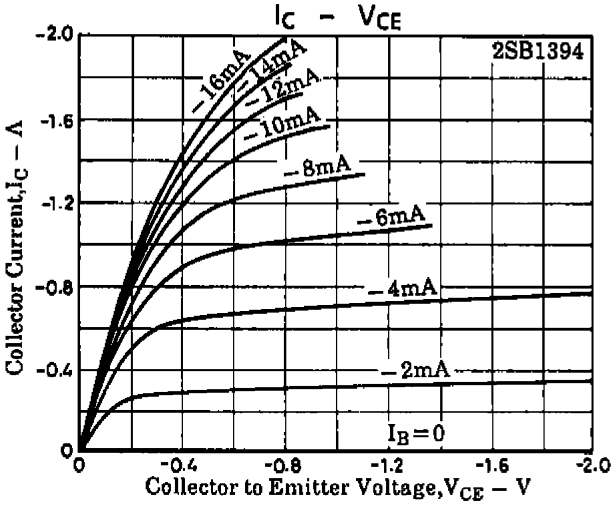
■ Marking

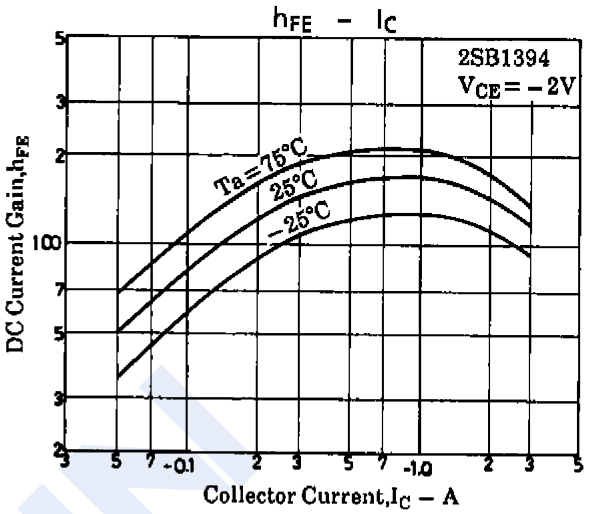
Marking	BN

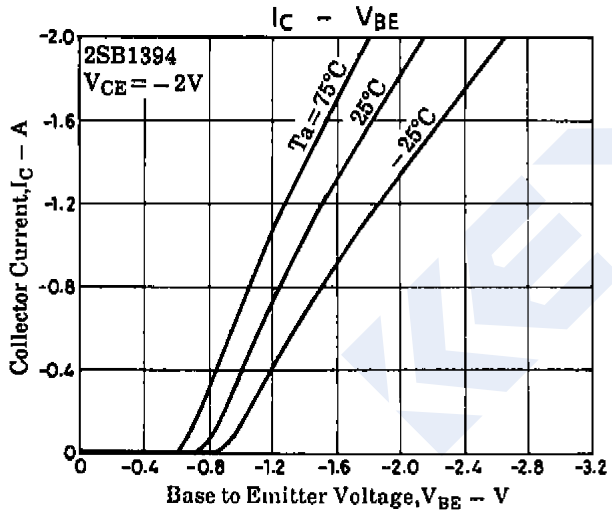
PNP Transistors

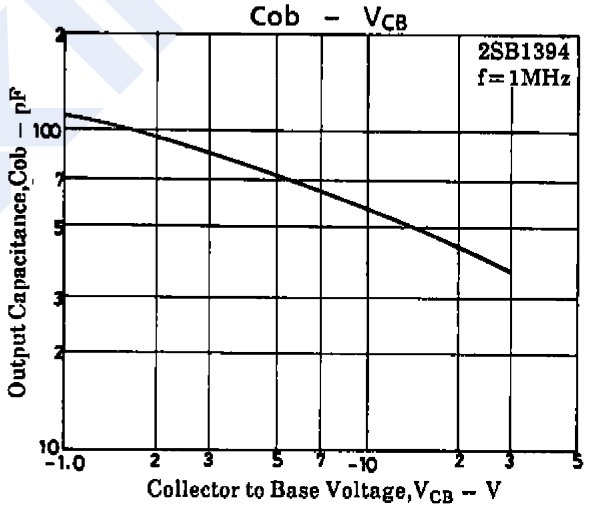
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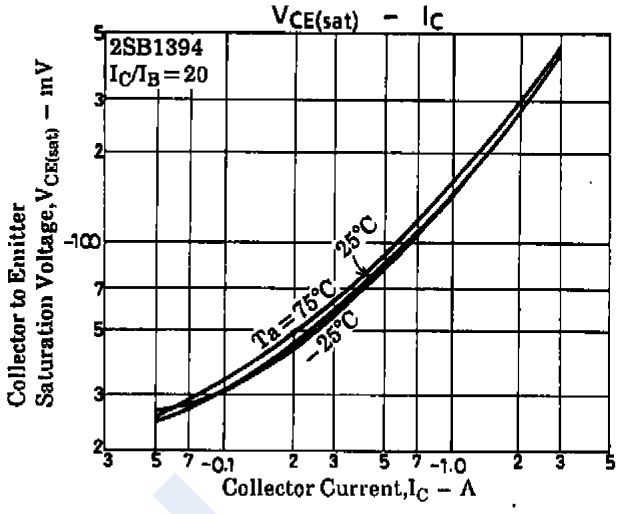
■ Typical Characterisitics

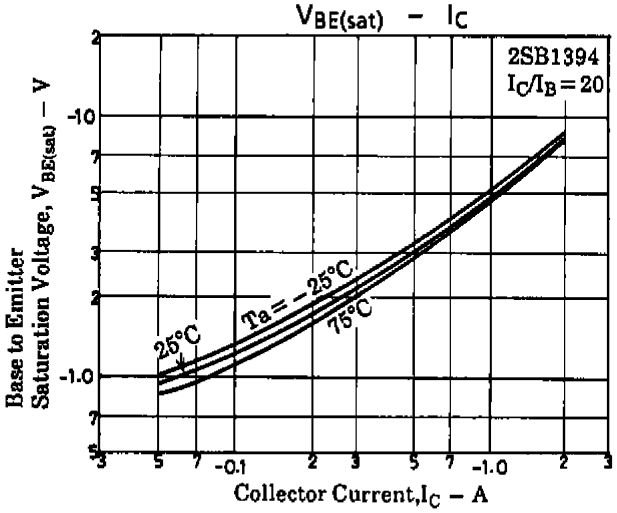












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■ Typical Characterisitics

